AKN62308B Series

1048576-Word × 8-Bit CMOS Mask Programmable ROM

AKN62308BP/BF Series is a 8-Mbit CMOS mask-programable ROM organized as 1048576-word x 8-bits. It can be operated with a battery because of low power consumption. The large capacity of 8M bits is optimum for a kanji character generator.

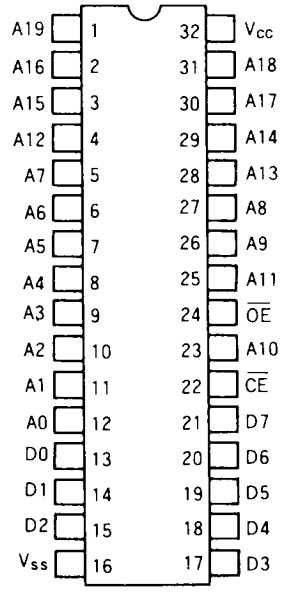
Features

- Single 5 V
- Wired OR is permitted for the output in three states
- TTL compatible
- Address access time: 200 ns (max.)
- Low power: Active 100 mW (typ)
  Standby 5 μW (typ)
- Byte-Wide Data Organization
- JEDEC PIN ORGANIZATION

Ordering Information

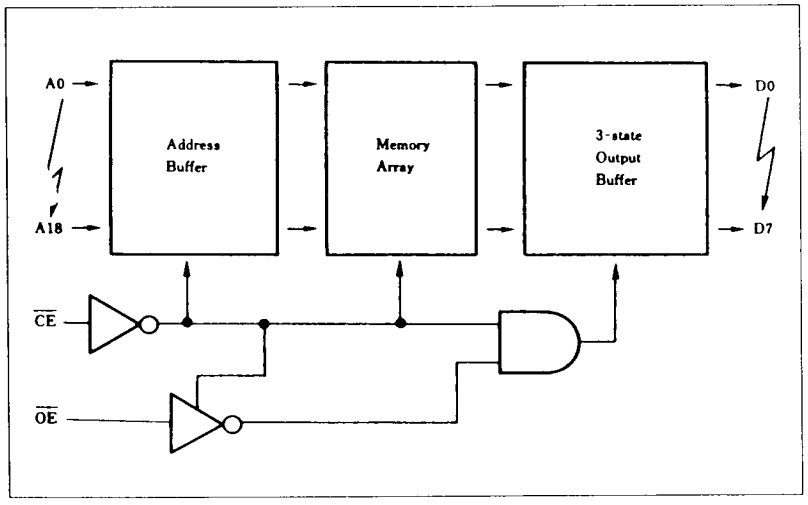
Type No.	Address Access Time	Package
AKN62308BP	200 ns	600 mil 32-pin plastic DIP
AKN62308BF	200 ns	32-pin plastic SOP

PIN CONFIGURATION



(Top View)

Block Diagram



Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Power supply voltage*1	V_{CC}	–0.3 to +7.0	V
Terminal voltage*1	V_T	–0.3 to V_{CC} + 0.3	V
Operating temperature	Topr	0 to +70	°C
Storage temperature	Tstg	–55 to +125	°C
Bias temperature	Tbias	–20 to +85	°C

Note: *1. With respect to V_{SS}.

Recommended Operating Conditions (V_{SS} = 0 V, Ta = 0 to +70°C)

Item	Symbol	Min	Typ	Max	Unit
Power supply voltage	V_{CC}	4.5	5.0	5.5	V
Input voltage	V_{IH}	2.2	—	V_{CC} + 0.3	V
	V_{IL}	–0.3	—	0.8	V

DC Characteristics (V_{CC} = 5 V ± 10%, V_{SS} = 0 V, Ta = 0 to +70°C)

Item		Symbol	Min	Max	Unit	Test Conditions
Power supply current	Active	I_{CC}	—	50	mA	V_{CC} = 5.5 V, I_{DOUT} = 0 mA, t_{RC} = Min
	Standby	I_{SB}	—	30	µA	V_{CC} = 5.5 V, $\overline{CE} \geq V_{CC}$ – 0.2 V
Input leak current		$\lvert I_{LI} \rvert$	—	10	µA	V_{IN} = 0 to V_{CC}
Output leak current		$\lvert I_{LO} \rvert$	—	10	µA	$\overline{CE}$ = 2.2 V, V_{OUT} = 0 to V_{CC}
Output voltage		V_{OH}	2.4	—	V	I_{OH} = –205 µA
		V_{OL}	—	0.4	V	I_{OL} = 1.6 mA

Capacitance (V_{CC} = 5 V ± 10%, V_{SS} = 0 V, Ta = 25°C, Vin = 0 V, f = 1 MHz)

Item	Symbol	Min	Max	Unit
Input capacitance*1	Cin	—	15	pF
Output capacitance*1	Cout	—	15	pF

Note: *1. This parameter is sampled and not 100% tested.

AC Operating Characteristics (V_{CC} = 5 V ± 10%, V_{SS} = 0 V, Ta = 0 to +70°C)

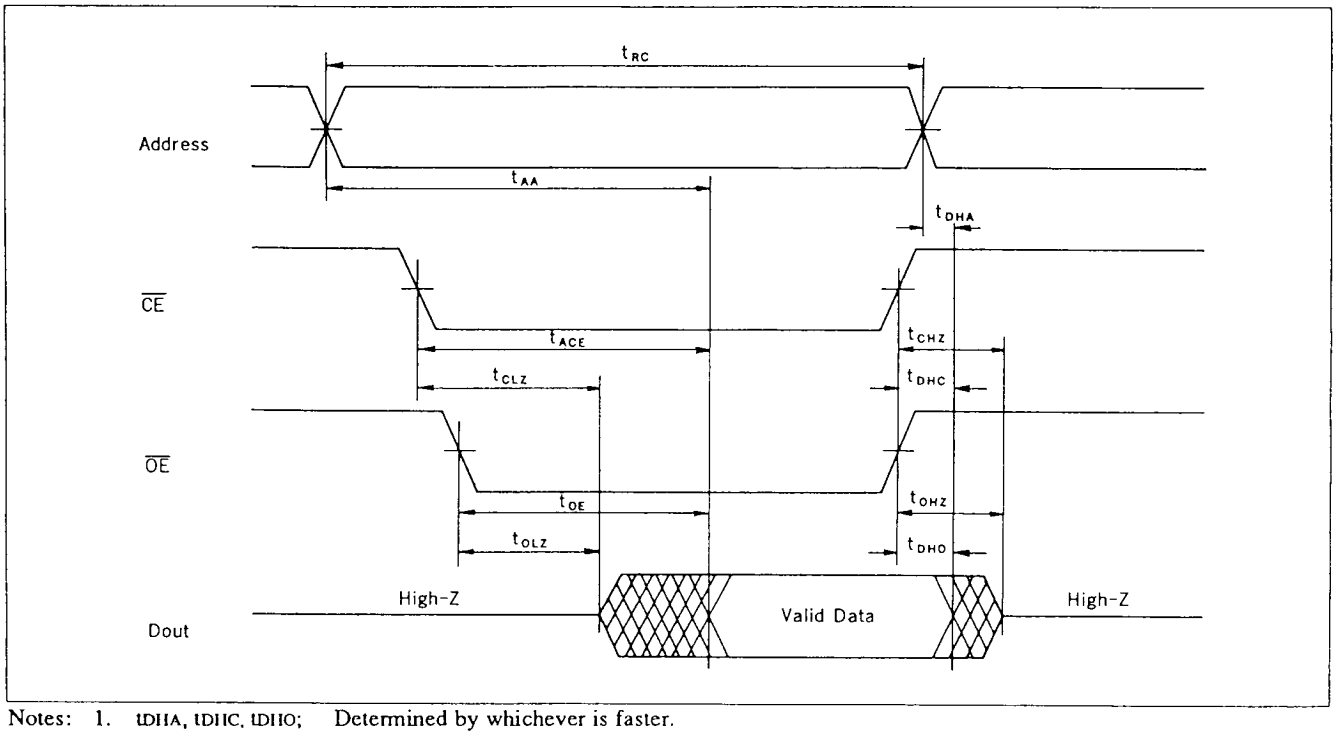
Test Conditions

Input pulse level: 0.8 to 2.4 V
I/O timing reference level: 1.5 V
Input rise/fall time: 10 ns
Output load: 1 TTL gate + C_L = 100 pF (including jig capacitance)

Item	Symbol	AKN62308B		Unit
		Min	Max	
Cycle time	t_{RC}	200	—	ns
Address access time	t_{AA}	—	200	ns
$\overline{CE}$ access time	t_{ACE}	—	200	ns
$\overline{OE}$ access time	t_{OE}	—	100	ns
Output Hold Time from Address Change	t_{DHA}	0	—	ns
Output Hold Time from $\overline{CE}$	t_{DHC}	0	—	ns
Output Hold Time from $\overline{OE}$	t_{DHO}	0	—	ns
$\overline{CE}$ to Output in High Z	t_{CHZ}*1	—	70	ns
$\overline{OE}$ to Output in High Z	t_{OHZ}*1	—	70	ns
$\overline{CE}$ to Output in Low Z	t_{CLZ}	10	—	ns
$\overline{OE}$ to Output in Low Z	t_{OLZ}	10	—	ns

Note: *1 t_{CHZ} and t_{OHZ} define the time at which the output goes to the high impedance state and is not referenced to output voltage level.

Timing Waveform



Notes: 1. t_{DHA}, t_{DHC}, t_{DHO}; Determined by whichever is faster.
2. t_{AA}, t_{ACE}, t_{OE}; Determined by whichever is slower.
3. t_{CLZ}, t_{OLZ}; Determined by whichever is slower.